

isc Silicon PNP Power Transistor

2SA1492

DESCRIPTION

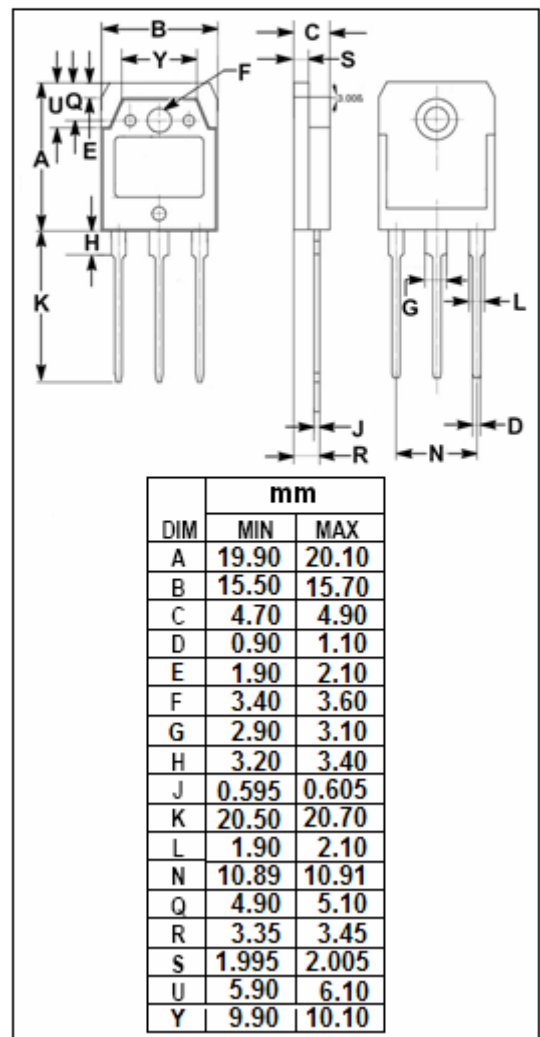
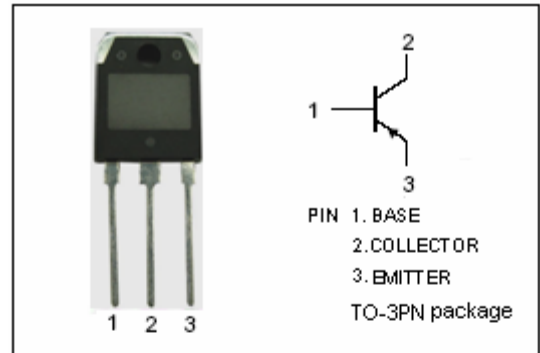
- High Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = -180V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Complement to Type 2SC3856

APPLICATIONS

- For audio and general purpose applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER   | VALUE   | UNIT             |
|-----------|---|---------|------------------|
| $V_{CBO}$ | Collector-Base Voltage                                  | -180    | V                |
| $V_{CEO}$ | Collector-Emitter Voltage                               | -180    | V                |
| $V_{EBO}$ | Emitter-Base Voltage                                    | -6      | V                |
| $I_C$     | Collector Current-Continuous                            | -15     | A                |
| $I_B$     | Base Current-Continuous                                 | -4      | A                |
| $P_C$     | Collector Power Dissipation<br>@ $T_C=25^\circ\text{C}$ | 130     | W                |
| $T_J$     | Junction Temperature                                    | 150     | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature Range                               | -55~150 | $^\circ\text{C}$ |



## isc Silicon PNP Power Transistor

2SA1492

## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

| SYMBOL        | PARAMETER                            | CONDITIONS   | MIN  | TYP. | MAX  | UNIT          |
|---------------|--------------------------------------|--|------|------|------|---------------|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage  | $I_C = -50\text{mA}$ ; $I_B = 0$                         | -180 |      |      | V             |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = -5.0\text{A}$ ; $I_B = -0.5\text{A}$              |      |      | -2.0 | V             |
| $I_{CBO}$     | Collector Cutoff Current             | $V_{CB} = -180\text{V}$ ; $I_E = 0$                      |      |      | -100 | $\mu\text{A}$ |
| $I_{EBO}$     | Emitter Cutoff Current               | $V_{EB} = -6\text{V}$ ; $I_C = 0$                        |      |      | -100 | $\mu\text{A}$ |
| $h_{FE}$      | DC Current Gain                      | $I_C = -3\text{A}$ ; $V_{CE} = -4\text{V}$               | 50   |      | 180  |               |
| $C_{OB}$      | Output Capacitance                   | $I_E = 0$ ; $V_{CB} = -10\text{V}$ ; $f = 1.0\text{MHz}$ |      | 500  |      | pF            |
| $f_T$         | Current-Gain—Bandwidth Product       | $I_E = 0.5\text{A}$ ; $V_{CE} = -12\text{V}$             |      | 20   |      | MHz           |

## Switching times

|           |              |   |  |     |  |               |
|-----------|--------------|---|--|-----|--|---------------|
| $t_{on}$  | Turn-on Time | $I_C = -10\text{A}$ , $R_L = 4\Omega$ ,<br>$I_{B1} = -I_{B2} = -1\text{A}$ , $V_{CC} = -40\text{V}$ |  | 0.6 |  | $\mu\text{s}$ |
| $t_{stg}$ | Storage Time |   |  | 0.9 |  | $\mu\text{s}$ |
| $t_f$     | Fall Time    |   |  | 0.2 |  | $\mu\text{s}$ |

◆  $h_{FE}$  Classifications

| O      | P      | Y      |
|--------|--------|--------|
| 50-100 | 70-140 | 90-180 |

isc Silicon PNP Power Transistor

2SA1492

